STRUCTURE AND PROCESS FOR A CAPACITOR AND OTHER DEVICES

Abstract

A structure and method of fabrication of a capacitor and other devices by providing a semiconductor structure and providing a top insulating layer and conductive features over the semiconductor structure; forming a first conductive layer over the top insulating layer; patterning the first conductive layer to form at least a capacitor bottom plate and a first portion of the first conductive layer; forming a capacitor dielectric layer over the top insulating layer and the capacitor bottom plate and the first portion of the first conductive layer; forming a second conductive layer over the capacitor dielectric layer; and patterning the second conductive layer to form at least a top plate over the bottom plate and a first section of the second conductive layer on the capacitor dielectric layer. The embodiment can further comprise conductive features in the top insulating layer that can underlie the bottom plate, the first portion or/and the first section. The first portion and the first section can form resistors, capacitors or other devices.

FIGURE 8

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